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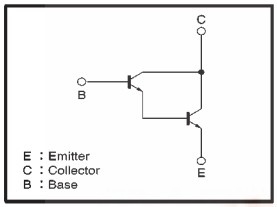
High-gain Amplifier Transistor (32V, 0.3A)
2SD2142K / 2SC2062S

●Features

1）Darlington connection for a high h_{FE}.
(DC current gain=5000(Min.) at V_{CE}=3V, I_C=0.1A)
2）High input impedance.

●Circuit diagram



●Absolute maximum ratings (Ta=25℃)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V_{CBO}	40	V
Collector-emitter voltage		V_{CEO}	32	V
Emitter-base voltage		V_{EBO}	12	V
Collector current		I_C	0.3	A
Collector power dissipation	2SD2142K	P_C	0.2	W
	2SC2062S		0.3	
Junction temperature		Tj	150	℃
Storage temperature		Tstg	−55～+150	℃

●Packaging specifications and h_{FE}

Type	2SD2142K	2SC2062S
Package	SMT3	SPT
h_{FE}	5k～	C
Code	T146	TP
Basic ordering unit (pieces)	3000	5000

●Electrical characteristics (Ta=25℃)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage		BV_{CBO}	40	—	—	V	I_C=100 μA
Collector-emitter breakdown voltage		BV_{CEO}	32	—	—	V	I_C=10mA
Emitter-base breakdown voltage		BV_{EBO}	12	—	—	V	I_E=100 μA
Collector cutoff current		I_{CBO}	—	—	0.1	μA	V_{CB}=30V
Emitter cutoff current		I_{EBO}	—	—	0.1	μA	V_{EB}=12V
DC current transfer ratio	2SD2142K	h_{FE}	5000	—	—	—	V_{CE}/I_C=3V/0.1A
	2SC2062S		10000	—	—	—	
Collector-emitter saturation voltage		$V_{CE(sat)}$	—	—	1.4	V	I_C/I_B=200mA/0.2mA
Transition frequency		f_T	—	200	—	MHz	V_{CE}=5V, I_E=−10mA, f=100MHz ✻
Output capacitance		Cob	—	2.5	—	pF	V_{CB}=10V, I_E=0A, f=1MHz

✻ Transition frequency of the device.

(94L-570-D25)

Low $V_{CE\,(sat)}$ Transistor (Strobes and DC/DC converters) (10V, 5A)
2SD2470

●Features

1）Low saturation voltage, typically $V_{CE\,(sat)}$ =0.25V at I_C / I_B=3A / 0.1A.
2）Collector current of 5A is possible.

●Absolute maximum ratings (Ta=25℃)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	15	V
Collector-emitter voltage	V_{CEO}	10	V
Emitter-base voltage	V_{EBO}	10	V
Collector current	I_C	5	A (DC)
	I_{CP}	8	A (Pulse) ✻
Collector power dissipation	P_C	0.4	W
Junction temperature	Tj	150	℃
Storage temperature	Tstg	−55～+150	℃

✻ Single pulse=10ms

●Packaging specifications and h_{FE}

Type	2SD2470
Package	SPT
h_{FE}	270～820
Code	TP
Basic ordering unit (pieces)	5000

●Electrical characteristics (Ta=25℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	10	—	—	V	I_C=1mA
Collector-emitter breakdown voltage	BV_{CEO}	15	—	—	V	I_C=50 μA
Emitter-base breakdown voltage	BV_{EBO}	10	—	—	V	I_E=50 μA
Collector cutoff current	I_{CBO}	—	—	0.1	μA	V_{CB}=10V
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	V_{EB}=8V
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	0.25	0.5	V	I_C/I_B=3/0.1A
DC current transfer ratio	h_{FE}	270	—	820	—	V_{CE}=2V, I_C=2A
Transition frequency	f_T	—	170	—	MHz	V_{CE}=6V, I_E=0.05A, f=100MHz
Output capacitance	Cob	—	30	—	pF	V_{CB}=10V, I_E=0A, f=1MHz

(SPEC-D230)

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